

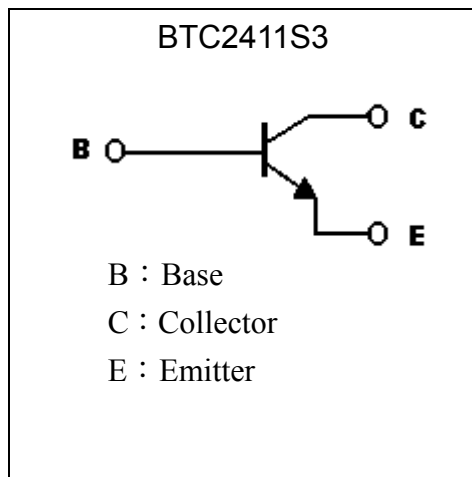
General Purpose NPN Epitaxial Planar Transistor

BTC2411S3

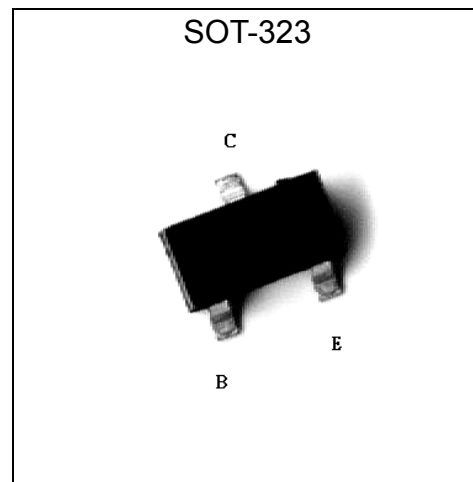
Description

- The BTC2411S3 is designed for general purpose amplifier applications. It is housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.
- Low $V_{CE(sat)}$
- Low leakage current
- High cutoff frequency
- Complementary to BTA1036S3
- Pb-free lead plating and halogen-free package

Symbol

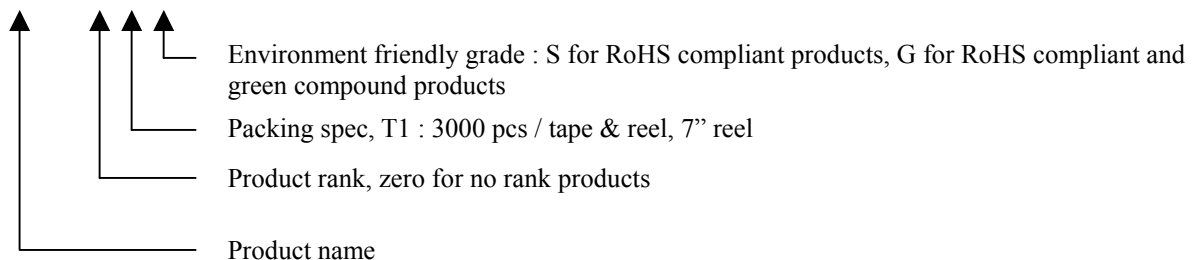


Outline



Ordering Information

Device	Package	Shipping
BTC2411S3-0-T1-G	SOT-323 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	600	mA
Power Dissipation @Ta=25°C Derate above 25°C	P _d	200 (Note 1)	mW
Operating Junction and Storage Temperature Range	T _j ; T _{stg}	-55~+150	°C

Note 1: when mounted on a FR-5 board with area measuring 1.0x0.75x0.062 in.

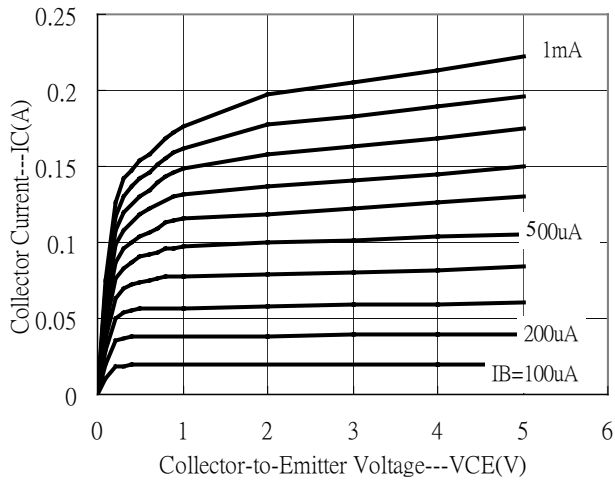
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	75	-	-	V	I _C =10μA
BV _{CEO}	50	-	-	V	I _C =1mA
BV _{EBO}	6	-	-	V	I _E =10μA
I _{CBO}	-	-	10	nA	V _{CB} =60V
I _{CEX}	-	-	10	nA	V _{CE} =60V, V _{EB(off)} =3V
I _{EBO}	-	-	100	nA	V _{EB} =3V
*V _{CE(sat)} 1	-	-	0.25	V	I _C =150mA, I _B =15mA
*V _{CE(sat)} 2	-	0.2	0.45	V	I _C =500mA, I _B =50mA
*V _{BE(sat)} 1	-	-	1.0	V	I _C =150mA, I _B =15mA
*V _{BE(sat)} 2	-	-	1.2	V	I _C =500mA, I _B =50mA
h _{FE1}	35	-	-	-	V _{CE} =10V, I _C =0.1mA
h _{FE2}	50	-	-	-	V _{CE} =10V, I _C =1mA
h _{FE3}	75	-	-	-	V _{CE} =10V, I _C =10mA
*h _{FE4}	100	-	300	-	V _{CE} =10V, I _C =150mA
*h _{FE5}	40	-	-	-	V _{CE} =10V, I _C =500mA
f _T	-	230	-	MHz	V _{CE} =20V, I _C =20mA, f=100MHz
C _{ob}	-	8.3	-	pF	V _{CB} =10V, I _E =0A, f=1MHz

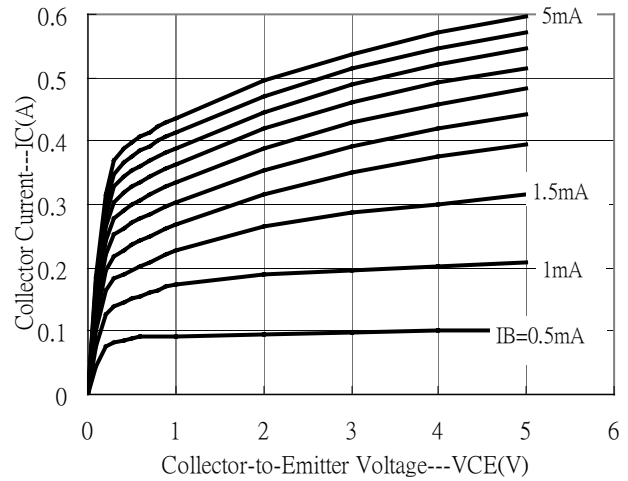
*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Typical Characteristics

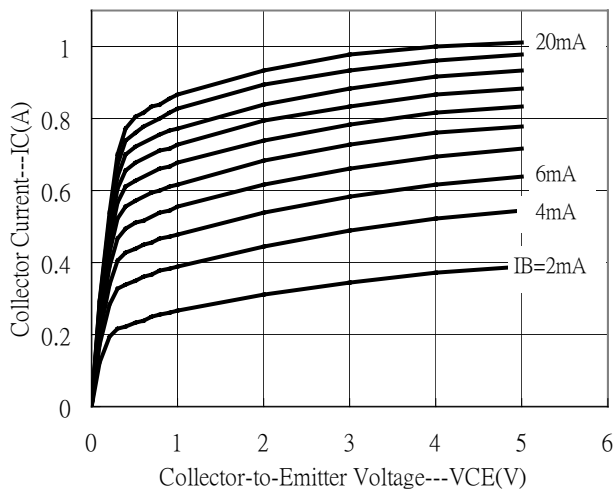
Emitter Grounded Output Characteristics



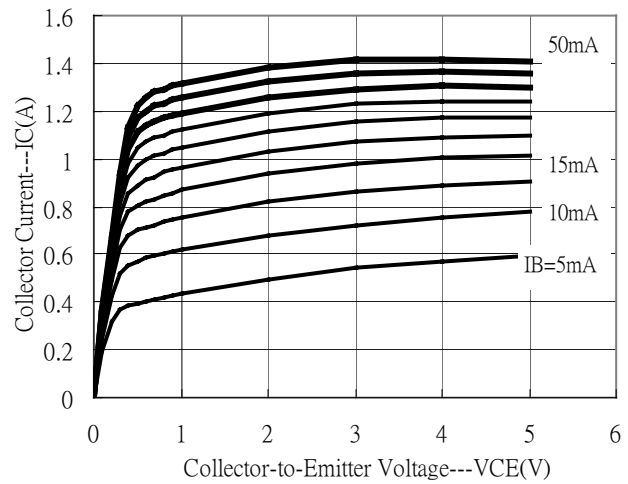
Emitter Grounded Output Characteristics



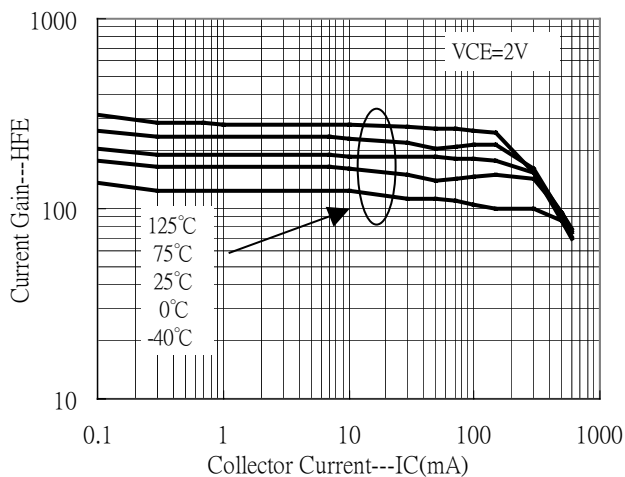
Emitter Grounded Output Characteristics



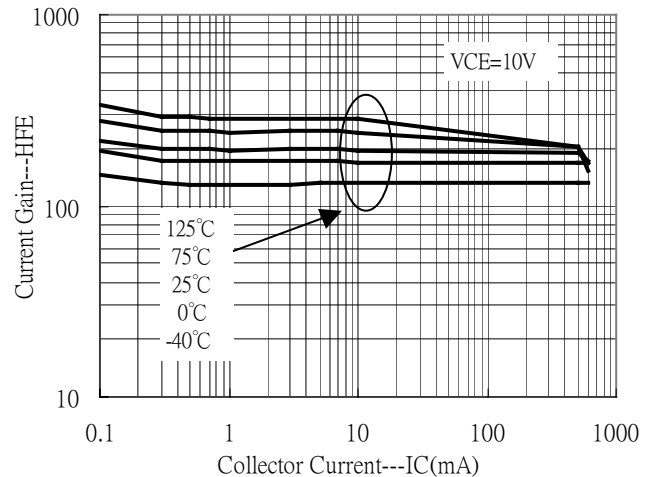
Emitter Grounded Output Characteristics



Current Gain vs Collector Current

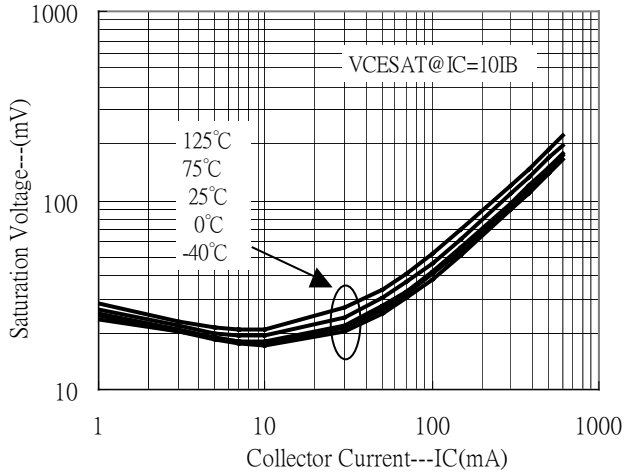


Current Gain vs Collector Current

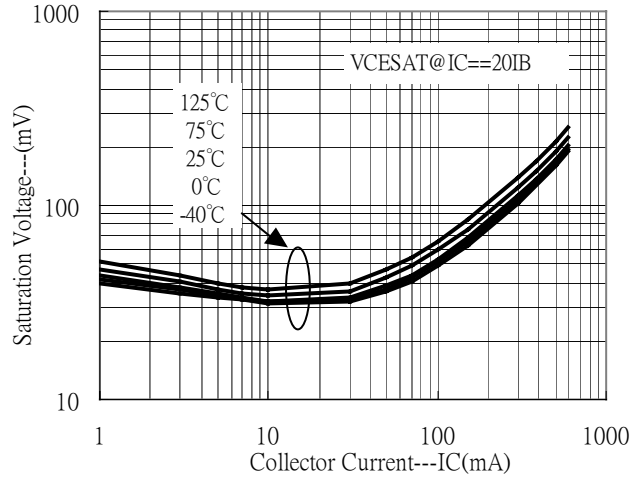


Typical Characteristics(Cont.)

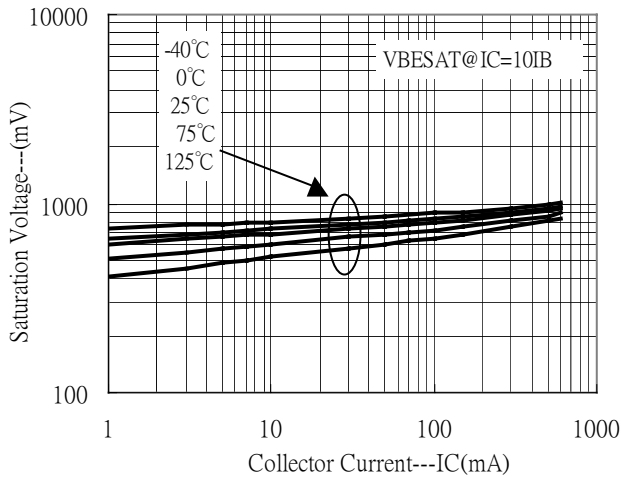
Saturation Voltage vs Collector Current



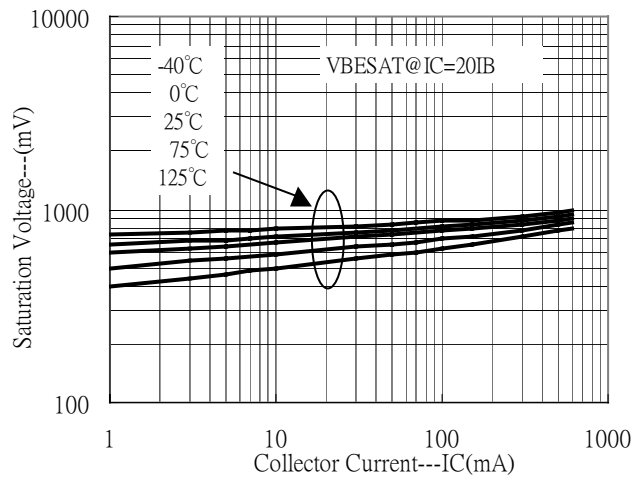
Saturation Voltage vs Collector Current



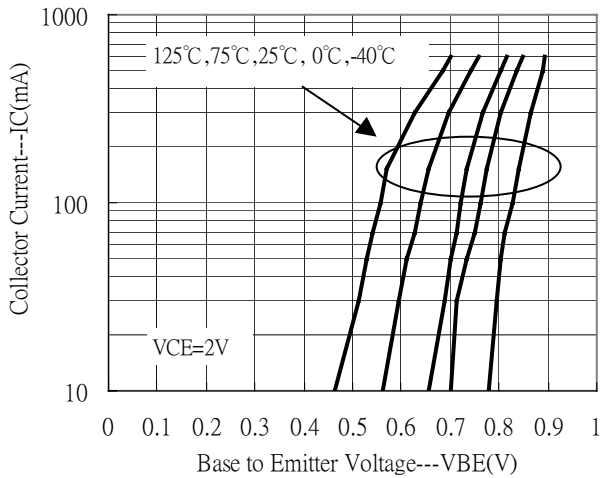
Saturation Voltage vs Collector Current



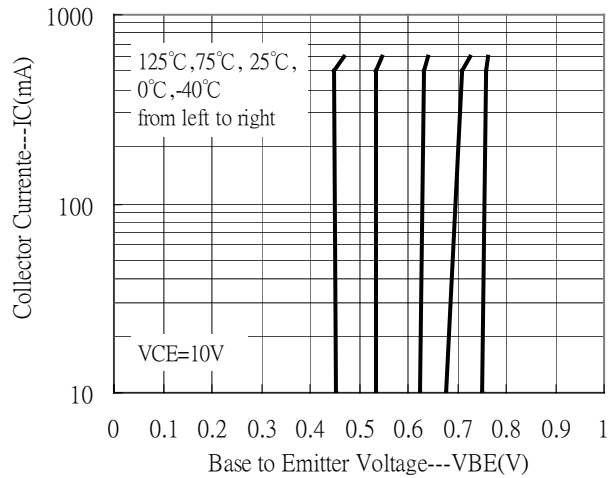
Saturation Voltage vs Collector Current



Base to Emitter Voltage vs Collector Current

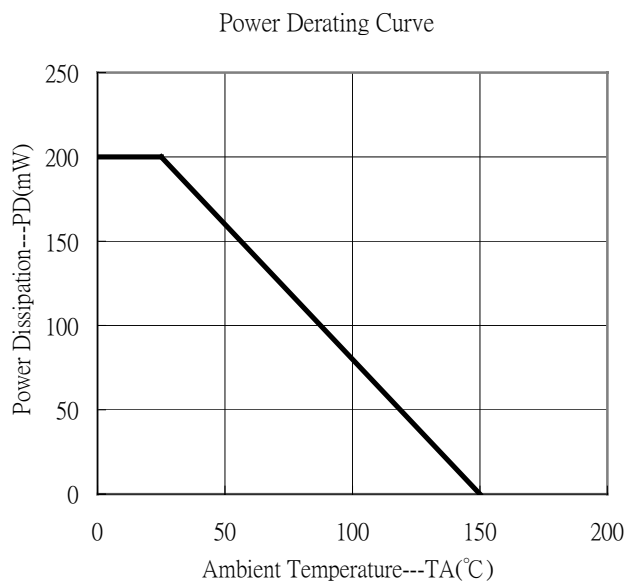
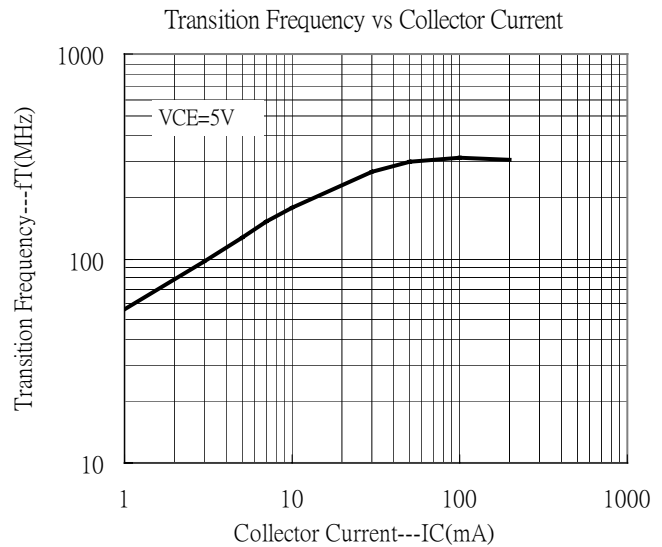
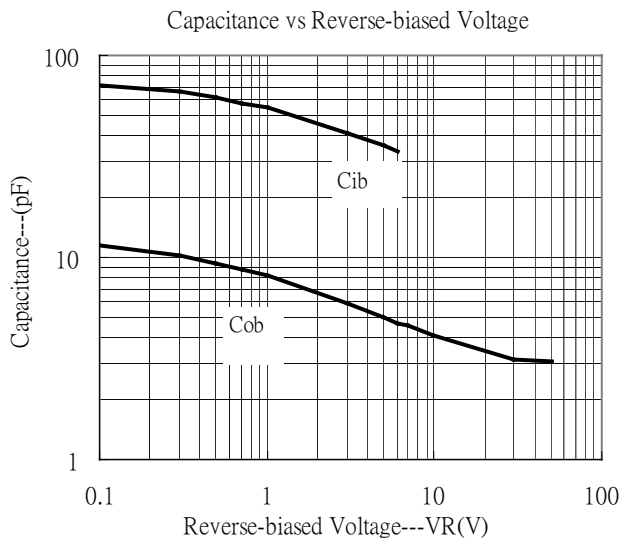


Base to Emitter Voltage vs Collector Current





Typical Characteristics(Cont.)

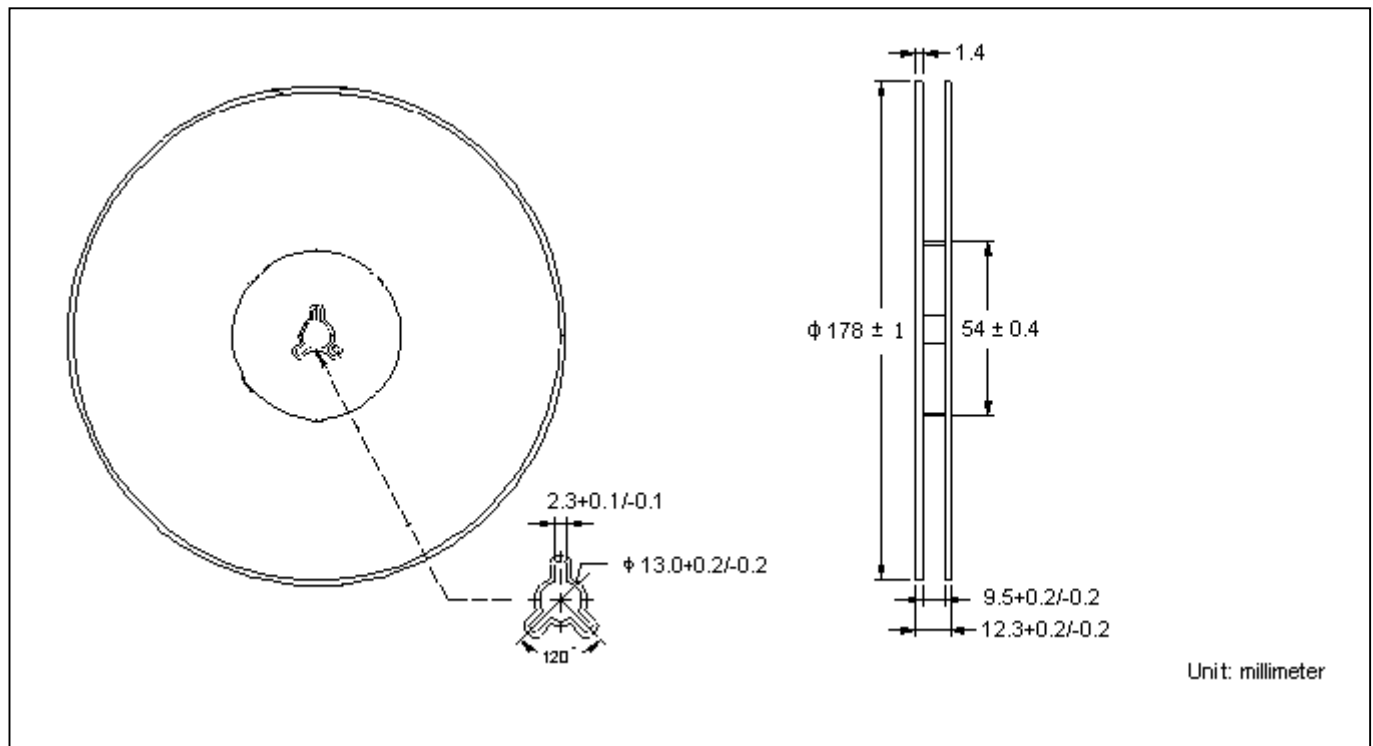




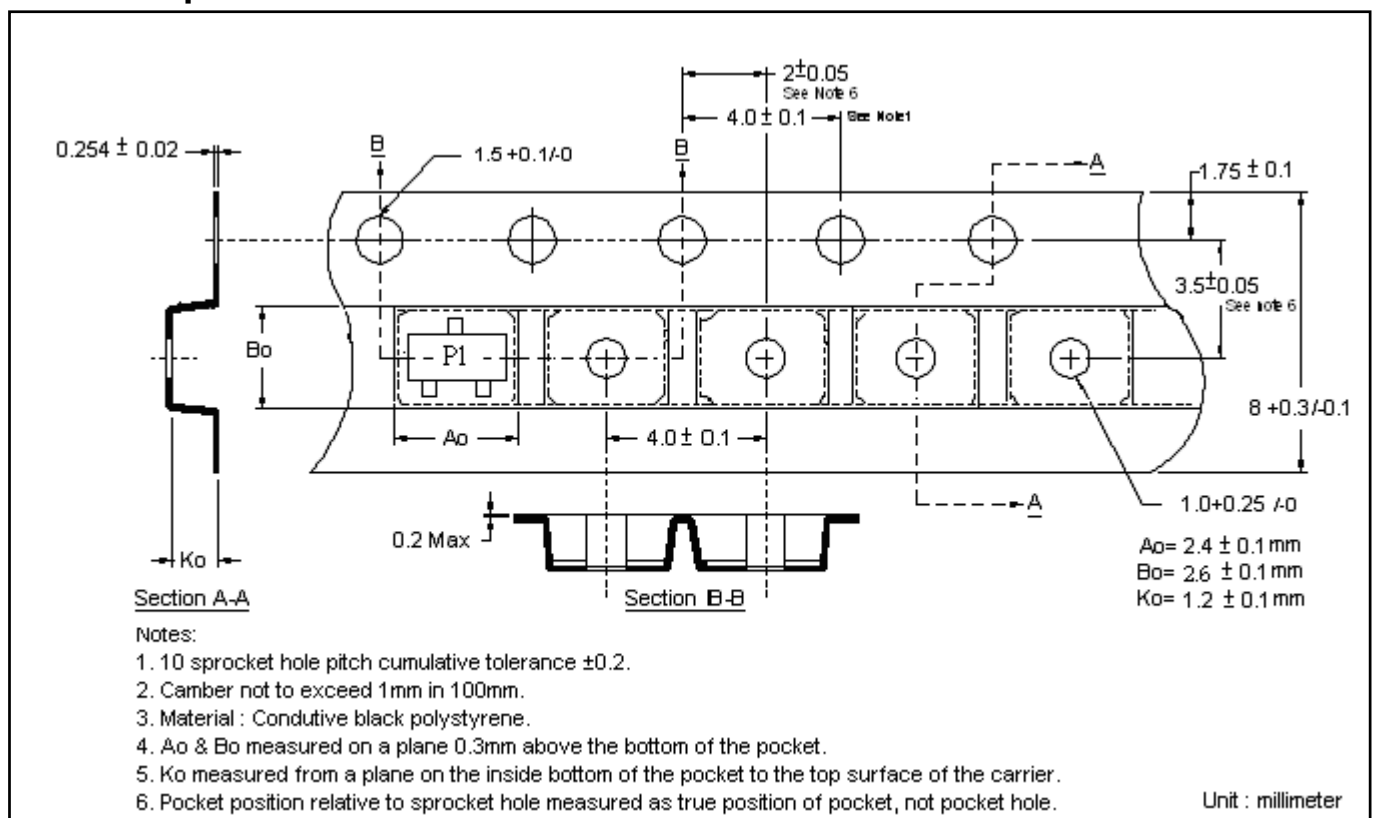
Spec. No. : C203S3-R
Issued Date : 2003.11.18
Revised Date : 2018.01.26
Page No. : 6/9

$$\left(\frac{\text{mm}}{\text{inches}}\right)$$

Reel Dimension

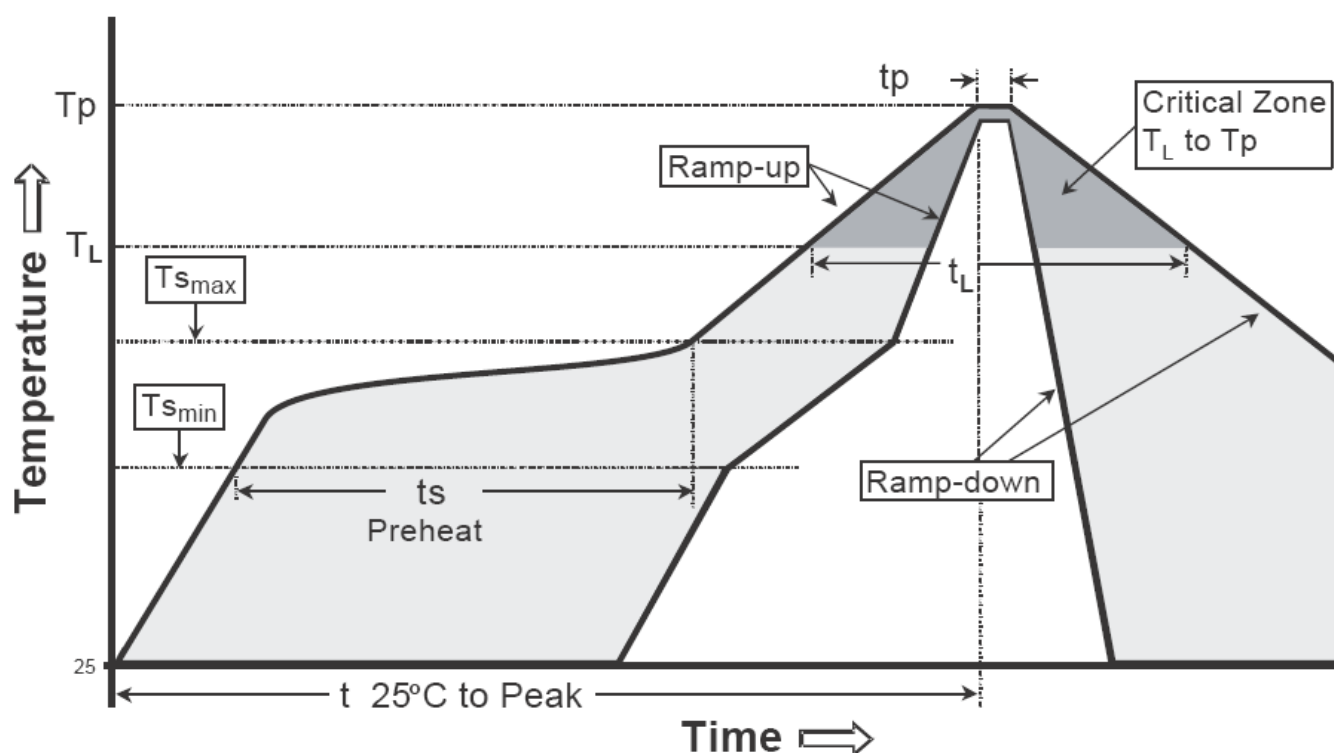


Carrier Tape Dimension



**Recommended wave soldering condition**

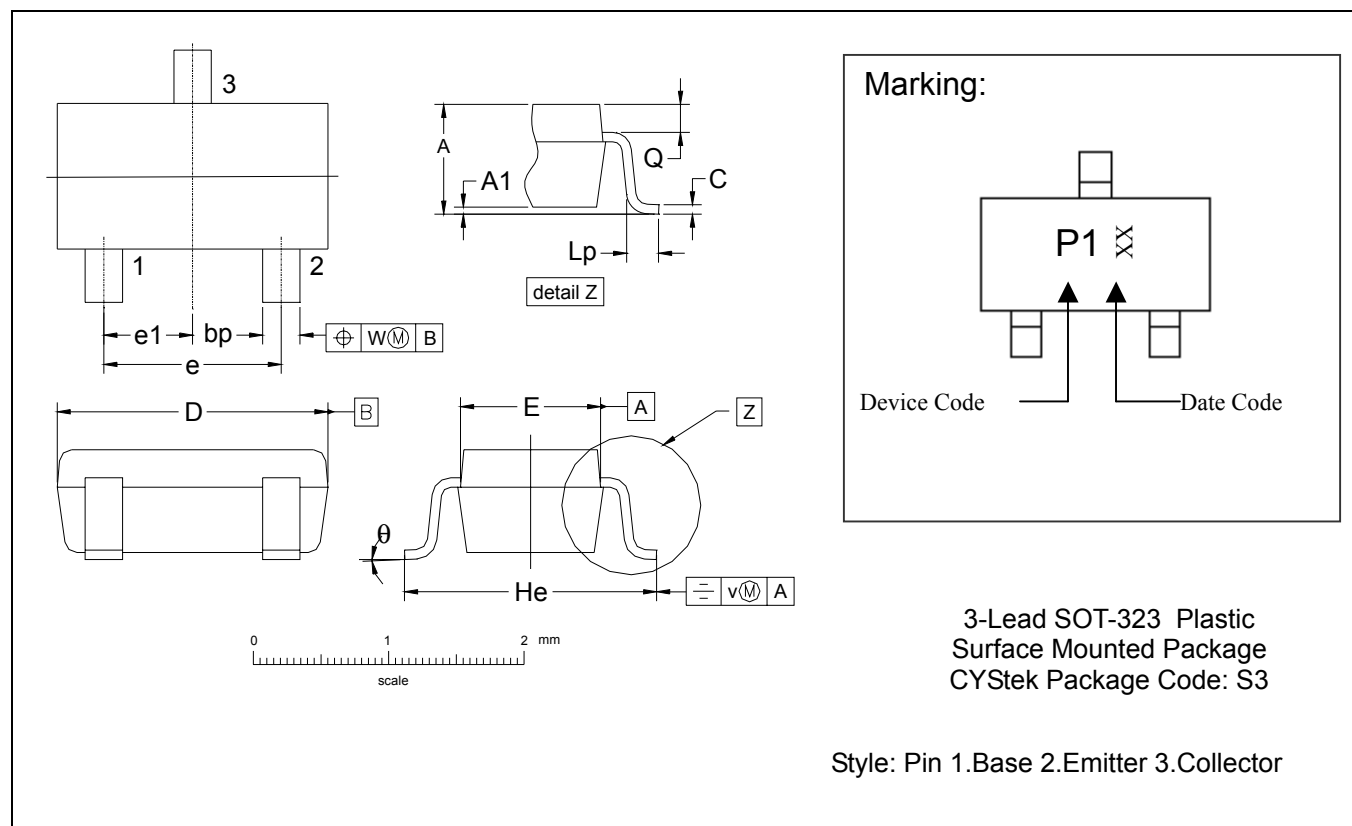
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-323 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0315	0.0433	0.80	1.10	e1	0.0256*		0.65*	
A1	0.0000	0.0039	0.00	0.10	He	0.0846	0.0965	2.15	2.45
bp	0.0078	0.0157	0.20	0.40	Lp	0.0105	0.0181	0.26	0.46
C	0.0031	0.0059	0.08	0.15	Q	0.0051	0.0091	0.13	0.23
D	0.0709	0.0866	1.80	2.20	v	0.0079	-	0.2	-
E	0.0453	0.0531	1.15	1.35	w	0.0079	-	0.2	-
e	0.0472	0.0551	1.20	1.40	θ	0°	8°	0°	8°

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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